

CLAIMS

We claim:

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A method for performing an ion implantation comprising:

providing a target chamber for containing a target for implantation and an ion source chamber including an ion source for generating an ion beam;

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providing a beam deceleration optics that includes a beam deceleration means in said ion source chamber for decelerating said ion beam for producing a low energy ion beam;

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providing a beam steering means to said beam deceleration optics to separate neutralized particles out of said ion beam by keeping said neutralized particles propagating in a neutralized-particle direction slightly different from a steered targeted ion-beam direction; and

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employing said ion-beam deceleration optics for transmitting said ion beam along said targeted ion-beam direction to said target for implantation and for blocking said neutralized particles from reaching said target for implantation.

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2. The method of performing an ion implantation of claim 1 wherein:

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providing an analyzer magnet to said ion source chamber for mass filtering.

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3. The method of performing an ion implantation of claim 1 wherein:

said step of employing said beam deceleration means further includes a step of providing a deceleration electric-field means for generating a deceleration electric-field for decelerating said ion beam for producing a low energy ion beam.

4. The method of performing an ion implantation of claim 1 wherein:

said step of employing said ion beam steering means for generating an electrostatic field for keeping said neutralized particle to transmit along a trajectory different than said ion beam carrying electric charges comprising a step of steering said ion beam to transmit in a targeted ion-beam direction slightly different from said neutralized-particle direction.

5. The method of performing an ion implantation of claim 1 wherein:

said step of employing an ion-beam deceleration optics further includes a step of employing a neutralized beam blocking means for blocking said neutralized particle from reaching said target of implantation in said target chamber.

6. The method of performing an ion implantation of claim 1 wherein:

5 said step of providing an ion source in an ion source chamber is a step of providing an ion source for generating a positive charged ion beam; and

10 said step of employing said beam deceleration means includes the step of employing a deceleration electric-field means for generating a negative electric-field for decelerating said ion beam for producing a low energy ion beam.

- 15 7. The method of performing an ion implantation of claim 1 wherein:

20 said step of employing said ion beam steering means comprising a step of steering said ion beam carrying electric charges to transmit in said targeted ion-beam direction at a small deflected angle.

- 25 8. The method of performing an ion implantation of claim 7 wherein:

30 said step of employing said ion beam steering means to steer said ion beam carrying electric charges to transmit in said targeted ion-beam direction comprising a step of steering said ion beam at a small deflected angle in a range of three to fifteen degrees relative to the horizontal axis.

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- said step of providing said ion source in said ion source chamber comprising a step of providing said ion source chamber and said target chamber with a vacuum in the range of 10^{-5} Torr; and

said step of employing said ion beam deceleration means comprising a step of decelerating said ion beam to an energy level as low as about 200 eV with an energy contamination of less than about 0.1%.

- employing a beam deceleration means for decelerating said ions projected from said ion source;

employing a beam steering means for generating an electrostatic field for separating a plurality of neutralized particles from said ion ions by keeping said neutralized particles propagating in a neutralized-particle direction slightly different from a targeted ion-beam direction of said ions.

- arranging a wafer implant position corresponding to said targeted ion-beam direction for accepting said ions projected thereto.

12. The method of claim 10 further comprising:
said step of transmitting said ions to a target of implantation
further comprising a step of employing a means for
blocking said neutralized particles from reaching said target
of implantation.
13. The method of claim 10 wherein:
said step of separating said neutralized particles from said
ions comprising a step of providing a charged particle
deflection means for deflecting said trajectory of said ions at
a small angle from said trajectory of said neutralized
particles.
14. The method of claim 10 further comprising:
configuring said ion beam deceleration means for
decelerating and processing said ions into an ion beam
having a large beam-height to beam-width ratio.
15. The method of claim 10 further comprising:
providing a beam block for blocking said neutralized
particles propagating in said neutralized-particle direction.
16. The method of claim 10 further comprising:
projecting said ions in forming said implantation ion beam
with high beam current and low and a ratio of a beam
height to a beam width equal or larger than 20.

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said step of providing a charged particle deflection means for deflecting said trajectory of said ions at a small angle from said trajectory of said neutralized particles comprising a step of deflecting said trajectory of said ions at an angle in the range of three to fifteen degrees.